MITSUBISHI SEMICONDUCTOR <GaAs FET>

MGFC39V6472A

6.4 ~ 7.2GHz BAND 8W INTERNALLY MATCHED GaAs FET

DESCRIPTION

The MGFC39V6472A is an internally impedance-matched GaAs power FET especially designed for use in 6.4 ~ 7.2 GHz band amplifiers. The hermetically sealed metalceramic package guarantees high reliability.

FEATURES

Class A operation Internally matched to 50(ohm) system High output power P1dB = 8W (TYP.) @ f=6.4~7.2GHz High power gain GLP = 9 dB (TYP.) @ f=6.4~7.2GHz High power added efficiency P.A.E. = 28 % (TYP.) @ f=6.4~7.2GHz Low distortion [item -51] IM3= -45 dBc(TYP.) @Po=28dBm S.C.L.

APPLICATION

item 01 : 6.4~7.2 GHz band power amplifier item 51 : 6.4~7.2 GHz band digital radio communication

QUALITY GRADE

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RECOMMENDED BIAS CONDITIONS

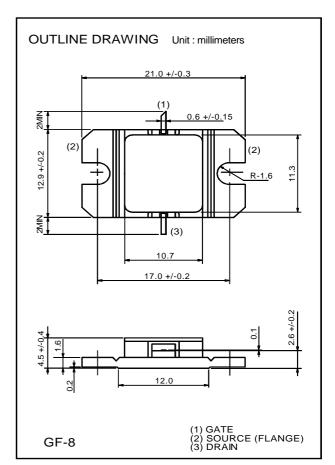
VDS = 10 (V)ID = 2.4 (A)Refer to Bias Procedure" RG= 50 (ohm)

ABSOLUTE MAXIMUM RATINGS (Ta=25 deg.C)

| Symbol | Parameter | Ratings | Unit | |
|--------|----------------------------|-----------------------|-------|--|
| VGDO | Gate to drain voltage | -15 | V | |
| VGSO | Gate to source voltage | -15 | V | |
| ID | Drain current | 7.5 | А | |
| IGR | Reverse gate current | erse gate current -20 | | |
| IGF | Forward gate current | 42 | mA | |
| PT | Total power dissipation *1 | 42.8 | W | |
| Tch | Channel temperature | 175 | deg.C | |
| Tstg | Storage temperature | -65 / +175 | deg.C | |



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| ECTRICAL CHARACTERISTICS | (Ta=25 deg.C) |
|--------------------------|---------------|

| Symbol | Parameter | Test conditions | Limits | | | Unit |
|---------------|---------------------------------------|--|--------|------|------|---------|
| | | | Min. | Тур. | Max. | Unit |
| IDSS | Saturated drain current | VDS=3V, VGS=0V | - | - | 7.5 | А |
| gm | Transconductance | VDS=3V, ID=2.2A | - | 2 | - | S |
| VGS(off) | Gate to source cut-off voltage | VDS=3V, ID=20mA | - | - | -4.5 | V |
| P1dB | Output power at 1dB gain compression | 1 | 38 | 39.5 | - | dBm |
| GLP | Linear power gain | VDS=10V, ID(RF off)=2.4A, f=6.4~7.2GHz | 7 | 9 | - | dB |
| ID | Drain current | | - | - | 3 | А |
| P.A.E. | Power added efficiency | | - | 28 | - | % |
| IM3 | 3rd order IM distortion *1 | | -42 | -45 | - | dBc |
| Rth(ch-c) | Thermal resistance *2 | Delta Vf method | - | - | 3.5 | deg.C/W |
| *1 · item -51 | 2 tone test Po=28dBm Single Carrier I | evel f-7.2GHz Delta f-10MHz | | | | |

1 : item -51, 2 tone test, Po=28dBm Single Carrier Level, f=7.2GHz, Delta t=10MHz

*2 : Channel to case



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